

In the Specification

The specification has been amended as follows:

Please delete paragraph [0029] on page 5 and replace it with the following paragraph:

In another aspect of the invention the seed layer comprises a lower TiW layer, an intermediate Cr/Cu layer and an upper Cu layer on which the solder—connect interconnect is formed. A nickel layer may be used on the Cu layer and then the solder interconnect formed on the nickel layer.

Please delete paragraph [0050] on page 8 and replace it with the following paragraph:

The predominant method of removing the seed layers above the lower TiW layer is electroetch. The electroetch process is very well known (for example as disclosed in U.S. Patent Nos. 5,543,032; 5,614,076; and 6,103,096; which patents are hereby incorporated by reference) and there are basically two types, the vertical electroetch (VEET) and the horizontal electroetch process (HEET). The etch processes are different in the conformation of the tool. In the case of the VEET tool the wafer sits vertically in the tool while the nozzle delivering electrolyte moves up and down over the surface of the wafer. In the HEET tool, the wafer sits horizontally with the nozzle spraying up onto the wafer as it moves across delivering the electrolyte.

Please delete paragraph [0054] on page 9 and replace it with the following paragraph:

It is conventional to use a methane sulfonic acid (MSA) clean in lead solder processing and such a clean may be used in conjunction with the oxalic acid clean of the invention. Acids other than MSA which may be used include tetrafluoroboric acid and trifluoroacetic ~~aid~~acid. It may be possible to combine the oxalic acid and MSA clean bath for certain applications.